

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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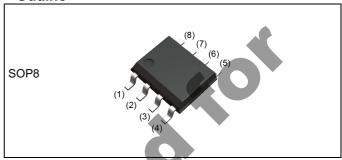
100V Nch+Pch Power MOSFET

	1	
Symbol	Tr1:Nch	Tr2:Pch
V_{DSS}	100V	-100V
R _{DS(on)} (Max.)	170mΩ	290mΩ
I_D	±3.0A	±2.5A
P_{D}	2.0)W

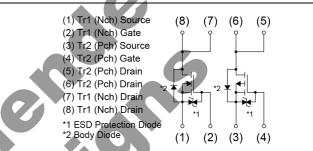
Features

- 1) Low on resistance
- 2) Small Surface Mount Package (SOP8)
- 3) Pb-free lead plating; RoHS compliant
- 4) Halogen Free

Outline



Inner circuit



Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	330
Туре	Tape width (mm)	12
	Basic ordering unit (pcs)	2500
	Taping code	ТВ
	Marking	SP8M51

Application

Switching

● Absolute maximum ratings (T_a = 25°C ,unless otherwise specified)

Parameter		Cymphol	Va	lue	Unit
		Symbol	Tr1:Nch	Tr2:Pch	Offic
Drain - Source voltage		V _{DSS}	100	-100	V
Continuous drain current		I _D	±3.0	±2.5	А
Pulsed drain current		I _{DP} *1	±12	±10	А
Gate - Source voltage		V_{GSS}	±20	±20	V
Dower discination	total	P _D *2	2.0		W
Power dissipation total		P _D *3	1	.4	VV
Junction temperature		T _j	15	50	°C
Operating junction and storage tem	perature range	T _{stg}	-55 to	+150	°C

●Thermal resistance

Davomotov		Cumphol		Values		Lloit
Parameter		Symbol	Min.	Тур.	Max.	Unit
Thermal registance in patient ambient	total	R_{thJA}^{*2}	-	-	62.5	°C/W
Thermal resistance, junction - ambient	total	R _{thJA} *3	-	-	89.2	C/VV

● Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Туре	Conditions		Values		Unit
r al al lie te i	Symbol	туре	Conditions	Min.	Týp.	Max.	Offic
Drain - Source breakdown	V	Tr1	$V_{GS} = 0V, I_D = 1mA$	100	-	-	V
voltage	V _{(BR)DSS}	Tr2	$V_{GS} = 0V$, $I_D = -1mA$	-100	-	-	V
Breakdown voltage	ΔV _{(BR)DSS}	Tr1	I _D = 1mA, referenced to 25°C		116.9	ı	mV/°C
temperature coefficient	ΔT_{j}	Tr2	$I_D = -1 \text{ mA}$, referenced to 25°C		-91.3	1	IIIV/ C
Zero gate voltage	ı	Tr1	$V_{DS} = 100V, V_{GS} = 0V$	-		1	
drain current	I _{DSS}	Tr2	$V_{DS} = -100V, V_{GS} = 0V$	4		-1	μA
Gate - Source	ı	Tr1	$V_{DS} = 0V$, $V_{GS} = \pm 20V$		-	±10	
leakage current	I _{GSS}	Tr2	$V_{DS} = 0V, V_{GS} = \pm 20V$	4	1	±10	μA
Gate threshold	V	Tr1	$V_{DS} = 10V, I_{D} = 1mA$	1.0	-	2.5	V
voltage	V _{GS(th)}	Tr2	$V_{DS} = -10V, I_{D} = -1mA$	-1.0	-	-2.5	V
Gate threshold voltage	$\Delta V_{GS(th)}$	Tr1	I _D = 1mA, referenced to 25°C	-1.02.5 3.6 - mV/°C			
temperature coefficient	ΔТј	Tr2	I _D = -1mA, referenced to 25°C	1	3.0	1	IIIV/ C
			$V_{GS} = 10V, I_D = 3.0A$	-	120	170	
		Tr1	$V_{GS} = 4.5 \text{V}, I_D = 3.0 \text{A}$	ı	130	180	
Static drain - source	D *4		$V_{GS} = 4.0V, I_D = 3.0A$	1	135	190	mΩ
on - state resistance	R _{DS(on)} *4		$V_{GS} = -10V, I_D = -2.5A$	ı	210	290	11122
		Tr2	V_{GS} = -4.5V, I_{D} = -1.25A	1	230	320	
			$V_{GS} = -4.0V, I_D = -1.25A$	-	240	340	
Cata registance	P	Tr1	f-1MHz open drain	-	6.9	-	Ω
Gate resistance	R_{G}	Tr2	f=1MHz, open drain	-	6.8	•	7.2
Forward Transfer	Y _{fs} *4	Tr1	$V_{DS} = 10V, I_{D} = 3.0A$	3.5	-	-	S
Admittance	l 'tsl	Tr2	$V_{DS} = -10V, I_{D} = -2.5A$	3.5	-	-	<u> </u>

^{*1} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*2} Mounted on a ceramic board (30×30×0.8mm)

^{*3} Mounted on a FR4 (25×25×0.8mm)

^{*4} Pulsed

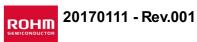
● Electrical characteristics (T_a = 25°C)

<Tr1>

Doromotor	Cumbal	Conditions	,	Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C _{iss}	V _{GS} = 0V	-	610	1	4
Output capacitance	C _{oss}	V _{DS} = 25V	-	55	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	35		
Turn - on delay time	$t_{d(on)}^{*4}$	$V_{DD} \simeq 50V$, $V_{GS} = 10V$	-	13	-	
Rise time	t _r *4	I _D = 1.5A	-	13	-	
Turn - off delay time	t _{d(off)} *4	$R_L = 33\Omega$	A-0	50	-	ns
Fall time	t _f *4	$R_G = 10\Omega$		14	-	

<Tr2>

Parameter	Symbol	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C _{iss}	V _{GS} = 0V		1550	-	
Output capacitance	C _{oss}	$V_{GS} = 0V$ $V_{DS} = -25V$	-	65	-	pF
Reverse transfer capacitance	C _{rss}	f=1MHz	-	40	-	
Turn - on delay time	t _{d(on)} *4	$V_{DD} \simeq -50V$, $V_{GS} = -10V$	-	15	-	
Rise time	t _r *4	I _D = -1.25A	-	13	-	
Turn - off delay time	$t_{d(off)}^{*4}$	$R_L = 50\Omega$	-	75	-	ns
Fall time	t _f *4	$R_G = 10\Omega$	-	19	-	



● Gate charge characteristics (T_a = 25°C)

<Tr1>

Parameter Symbol Total gate charge Q_g^{*4}	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	UTIIL
Total gate charge	Q _g *4		-	8.5	-	
Gate - Source charge	Q _{gs} *4	$V_{DD} \simeq 50V, I_{D} = 3.0A$ $V_{GS} = 5V$	-	1.8		nC
Gate - Drain charge	Q _{gd} *4	VGS 0V	-	3.5	7	

<Tr2>

Doromotor	Cumbal	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q _g *4		J Y-	12.5	-	
Gate - Source charge	Q _{gs} *4	$V_{DD} \simeq -50V$, $I_D = -2.5A$ $V_{GS} = -5V$	-	3.8	-	nC
Gate - Drain charge	Q _{gd} *4	·GS 0.		3.2	-	

● Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

<Tr1>

Doromotor	Symbol	Conditions	,	Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	Is	T _a = 25°C	-	-	1.0	^
Pulse forward current	I _{SP} *1	$I_a = 25^{\circ}C$	-	-	12	A
Forward voltage	V _{SD} *4	$V_{GS} = 0V, I_{S} = 3.0A$	-	-	1.2	V

<Tr2>

Downwater	Cymphal	Canditions	,	Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	I _S	T - 25°C	-	-	-1.0	^
Pulse forward current	I _{SP} *1	T _a = 25°C	-	-	-10	А
Forward voltage	V _{SD} *4	V _{GS} = 0V, I _S = -2.5A	-	-	-1.2	V

Fig.1 Power Dissipation Derating Curve

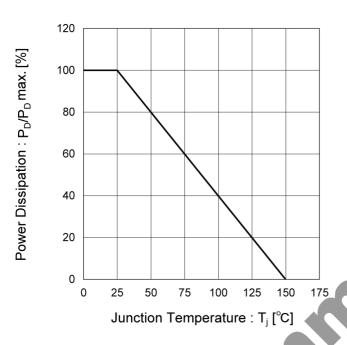
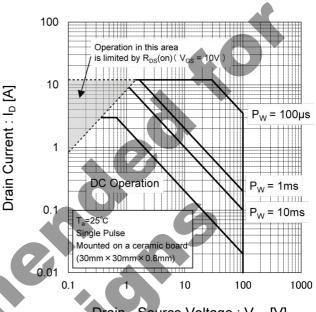


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

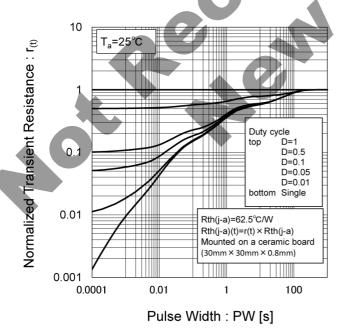
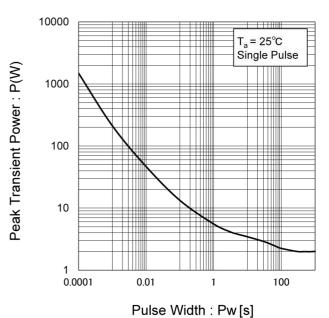


Fig.4 Single Pulse Maximum Power dissipation

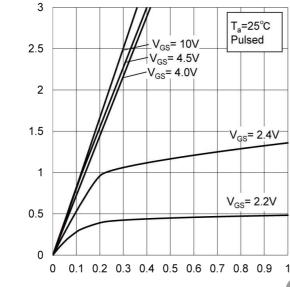


i dise width. i w[s]

Drain Current: I_D [A]

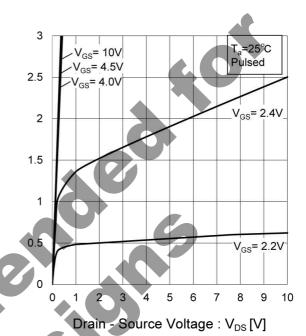
● Electrical characteristic curves < Tr1>

Fig.5 Typical Output Characteristics(I)



 $Drain - Source\ Voltage: V_{DS}[V]$

Fig.6 Typical Output Characteristics(II)



Drain Current : I_D [A]

Fig.7 Breakdown Voltage vs.

Junction Temperature

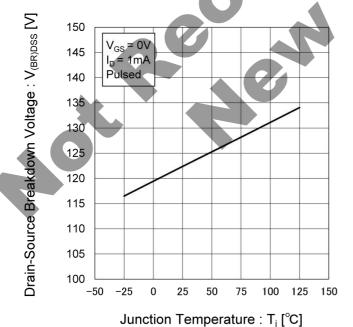


Fig.8 Typical Transfer Characteristics

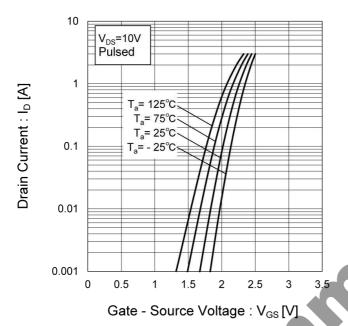
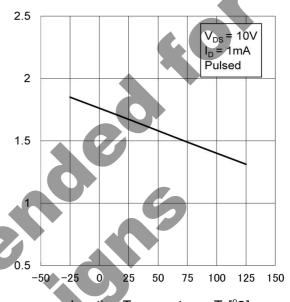


Fig.9 Gate Threshold Voltage vs.
Junction Temperature



Sate Threshold Voltage: VGS(th) [V]

Junction Temperature : T_j [°C]

Fig.10 Forward Transfer Admittance vs.

Drain Current

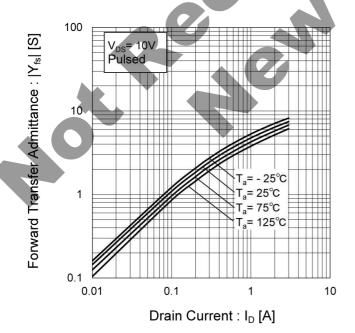


Fig.11 Drain Current Derating Curve

120 100 **Drain Current Dissipation** 80 : I_D/I_Dmax. [%] 60 40 20 0 125 -25 0 25 50 75 100 Junction Temperature : T_j [°C]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

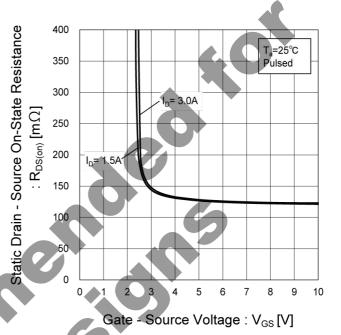


Fig.13 Static Drain - Source On - State

Resistance vs. Junction Temperature

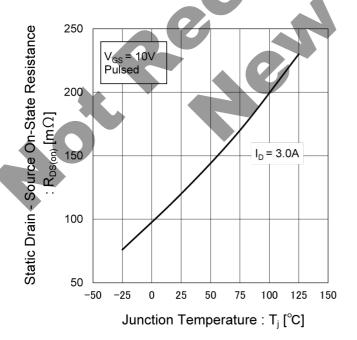


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I)

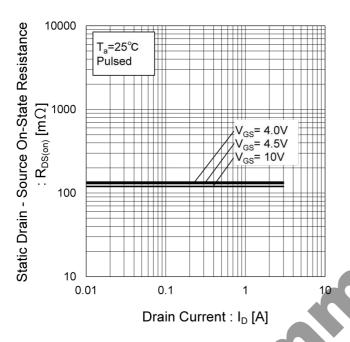


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

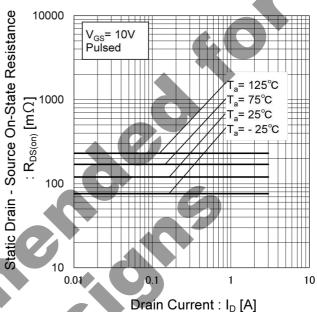
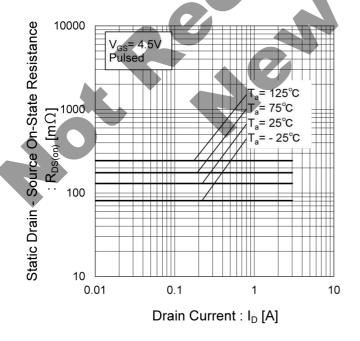


Fig.16 Static Drain - Source On - State

Resistance vs. Drain Current (III)

Fig.17 Static Drain - Source On - State
Resistance vs. Drain Current (IV)



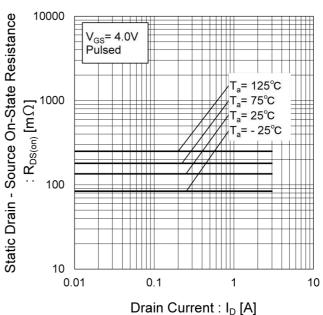


Fig.18 Typical Capacitance vs.

Drain - Source Voltage

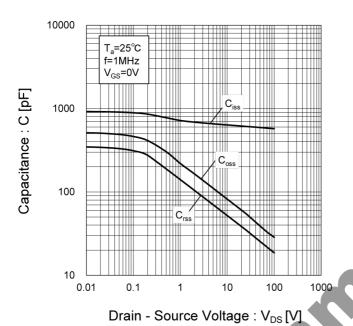


Fig.19 Switching Characteristics

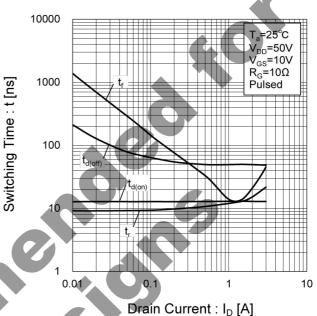


Fig.20 Dynamic Input Characteristics

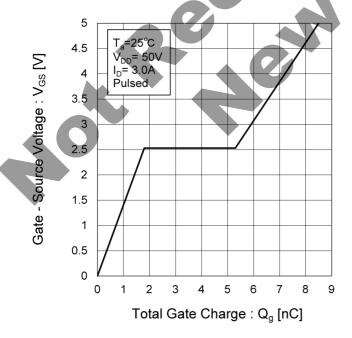


Fig.21 Source Current vs.

Source Drain Voltage

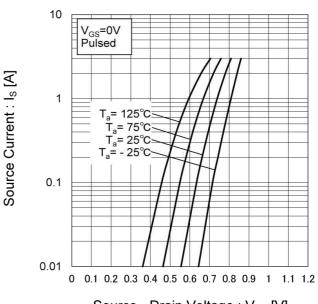


Fig.1 Power Dissipation Derating Curve

120
100
100
80
40
20
0 25 50 75 100 125 150 175
Junction Temperature : T_j [°C]

Fig.2 Maximum Safe Operating Area

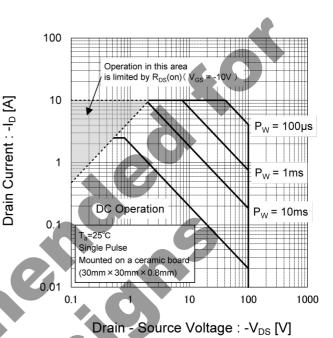


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

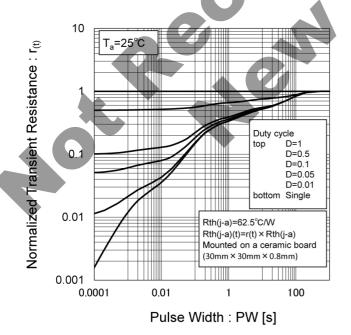


Fig.4 Single Pulse Maximum Power dissipation

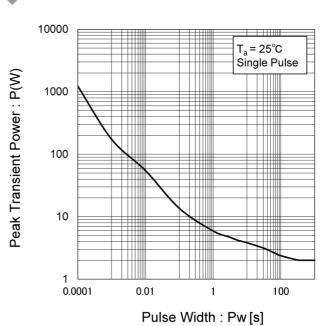
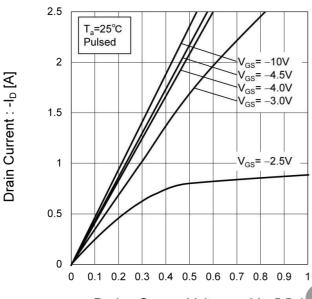
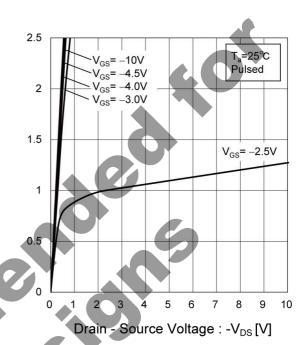


Fig.5 Typical Output Characteristics(I)



Drain - Source Voltage : $-V_{DS}[V]$

Fig.6 Typical Output Characteristics(II)



Drain Current : -I_D [A]

Fig.7 Breakdown Voltage vs.

Junction Temperature

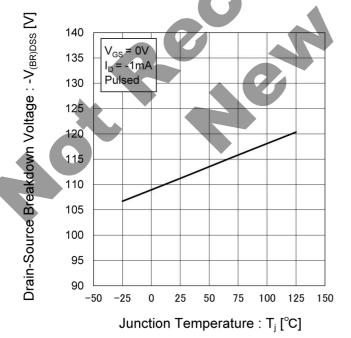
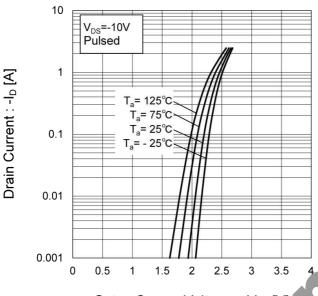


Fig.8 Typical Transfer Characteristics



Gate - Source Voltage : -V_{GS} [V]

Fig.9 Gate Threshold Voltage vs.
Junction Temperature

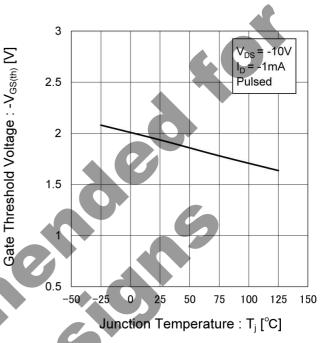


Fig.10 Forward Transfer Admittance vs.

Drain Current

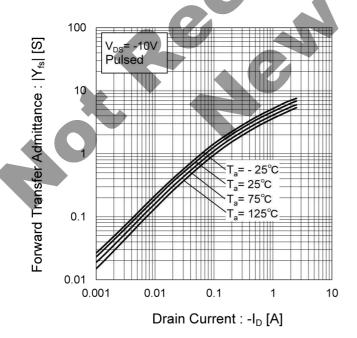


Fig.11 Drain Current Derating Curve

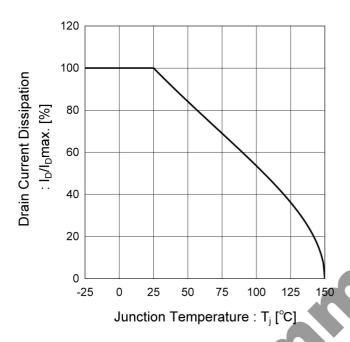


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

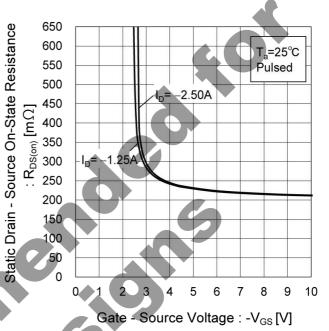


Fig.13 Static Drain - Source On - State

Resistance vs. Junction Temperature

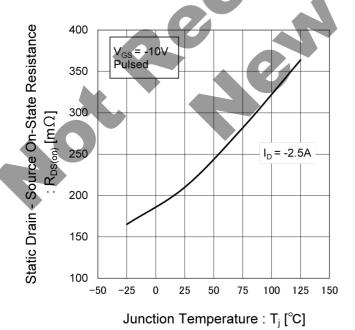


Fig.14 Static Drain - Source On - State
Resistance vs. Drain Current (I)

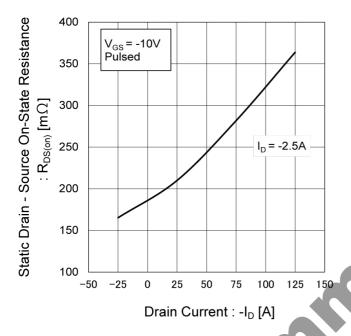


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

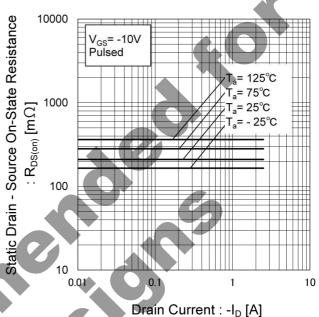
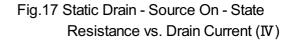
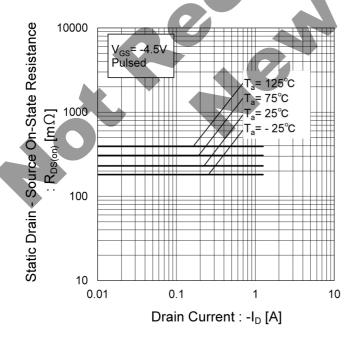


Fig.16 Static Drain - Source On - State

Resistance vs. Drain Current (III)





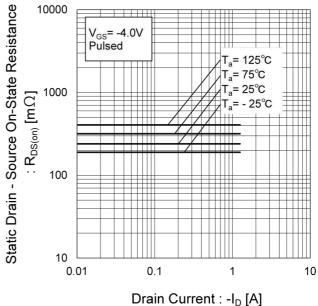


Fig.18 Typical Capacitance vs.

Drain - Source Voltage

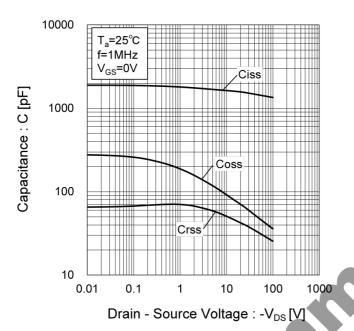


Fig.19 Switching Characteristics

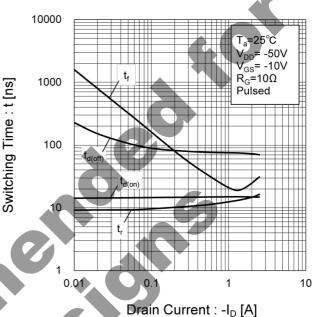


Fig.20 Dynamic Input Characteristics

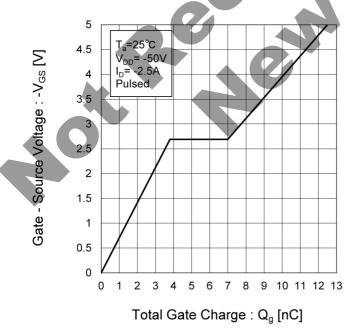
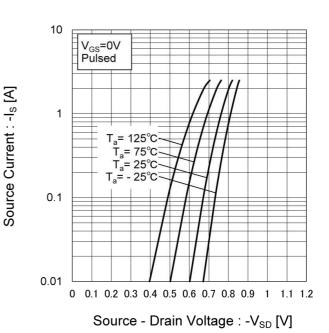


Fig.21 Source Current vs.

Source Drain Voltage



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● Measurement circuits <Tr1>

Fig.1-1 Switching Time Measurement Circuit

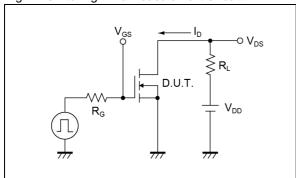


Fig.2-1 Gate Charge Measurement Circuit

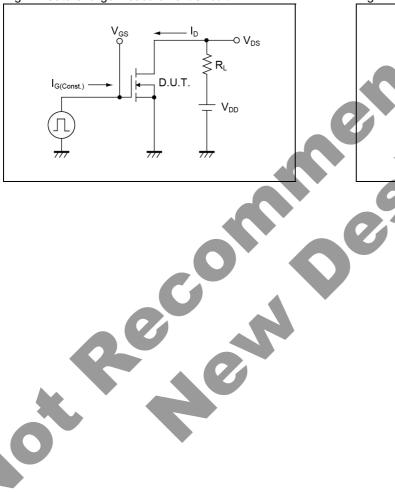


Fig.1-2 Switching Waveforms

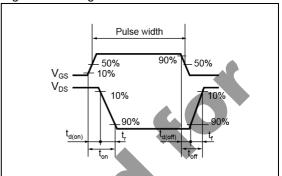
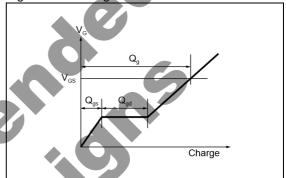


Fig.2-2 Gate Charge Waveform



● Measurement circuits < Tr2>

Fig.3-1 Switching Time Measurement Circuit

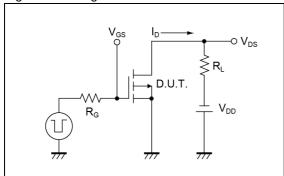


Fig.4-1 Gate Charge Measurement Circuit

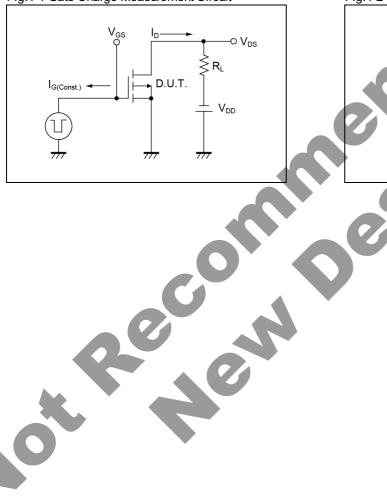


Fig.3-2 Switching Waveforms

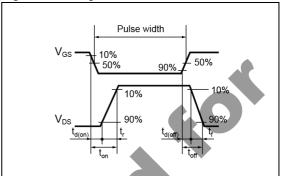
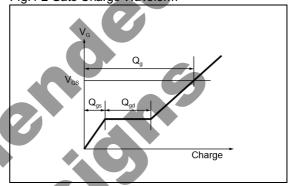
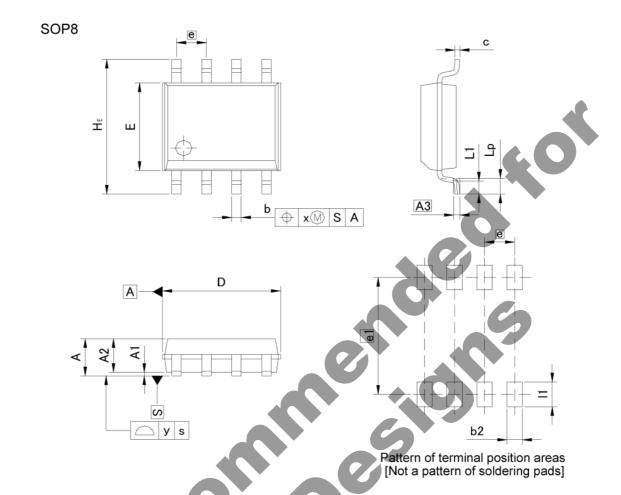


Fig.4-2 Gate Charge Waveform





Dimensions



DIM	MILIME	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	1	1.75	#	0.069
A1	0.	15	0.0	06
A2	1.40	1.60	0.055	0.063
A3	0,2	25	0.0	10
Ь	0.30	0.50	0.012	0.020
0	0.10	0.30	0.004	0.012
D	4.80	5.20	0.189	0.205
E	3.75	4.05	0.148	0.159
е	1.2	27	0.0	50
HE	5.70	6.30	0.224	0.248
L1	0.40	0.60	0.016	0.024
Lp	0.65	0.85	0.026	0.033
х	0.	15	0.0	06
У	0.1	10	0.0	04

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	=23	0.65	7 70	0.026
e1	5.15		0.203	
11		1.15	#3	0.045

Dimension in mm/inches

Notice

Precaution on using ROHM Products

1. Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JÁPAN	USA	EU	CHINA
CLASSⅢ	CL ACCTI	CLASS II b	СГАССШ
CLASSIV	CLASSⅢ	CLASSIII	CLASS III

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
 - [a] Installation of protection circuits or other protective devices to improve system safety
 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are designed and manufactured for use under standard conditions and not under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
 - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

Precaution for Product Label

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

Precaution for Foreign Exchange and Foreign Trade act

Since concerned goods might be fallen under listed items of export control prescribed by Foreign exchange and Foreign trade act, please consult with ROHM in case of export.

Precaution Regarding Intellectual Property Rights

- 1. All information and data including but not limited to application example contained in this document is for reference only. ROHM does not warrant that foregoing information or data will not infringe any intellectual property rights or any other rights of any third party regarding such information or data.
- 2. ROHM shall not have any obligations where the claims, actions or demands arising from the combination of the Products with other articles such as components, circuits, systems or external equipment (including software).
- No license, expressly or implied, is granted hereby under any intellectual property rights or other rights of ROHM or any third parties with respect to the Products or the information contained in this document. Provided, however, that ROHM will not assert its intellectual property rights or other rights against you or your customers to the extent necessary to manufacture or sell products containing the Products, subject to the terms and conditions herein.

Other Precaution

- 1. This document may not be reprinted or reproduced, in whole or in part, without prior written consent of ROHM.
- 2. The Products may not be disassembled, converted, modified, reproduced or otherwise changed without prior written consent of ROHM.
- In no event shall you use in any way whatsoever the Products and the related technical information contained in the Products or this document for any military purposes, including but not limited to, the development of mass-destruction weapons.
- 4. The proper names of companies or products described in this document are trademarks or registered trademarks of ROHM, its affiliated companies or third parties.

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General Precaution

- 1. Before you use our Products, you are requested to care fully read this document and fully understand its contents. ROHM shall not be in any way responsible or liable for failure, malfunction or accident arising from the use of any ROHM's Products against warning, caution or note contained in this document.
- 2. All information contained in this docume nt is current as of the issuing date and subject to change without any prior notice. Before purchasing or using ROHM's Products, please confirm the latest information with a ROHM sale s representative.
- 3. The information contained in this document is provided on an "as is" basis and ROHM does not warrant that all information contained in this document is accurate an d/or error-free. ROHM shall not be in an y way responsible or liable for any damages, expenses or losses incurred by you or third parties resulting from inaccuracy or errors of or concerning such information.

